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(54) VERTICAL THIN FILM SEMICONDUCTOR DEVICE

(57)Abstract:

PURPOSE: To provide a vertical thin film semiconductor device to which a large current can be made to flow without increasing the element dimension of the device.

CONSTITUTION: In a vertical TFT device, drain electrodes 11 and 12 and a source electrode 14 are laminated in the direction perpendicular to the surface of a substrate 10. The drain electrodes 11 and 12 are directly formed on the surface of the substrate 10 and the areas of the electrodes 11 and 12 are made larger than that of the source electrode 14.

